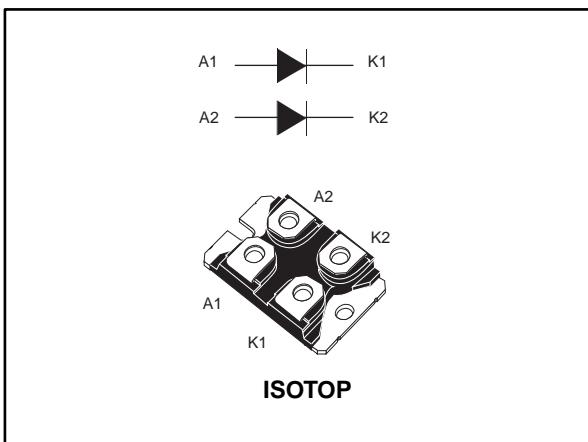


## Turbo 2 ultrafast high voltage rectifier

Datasheet - production data



### Features

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching and conduction losses
- Insulated package ISOTOP:
  - Insulated voltage: 2500 V<sub>RMS</sub> sine

### Description

This device, which uses ST Turbo 2 600 V technology, is especially suited for use in switching power supplies and industrial applications, like rectification and freewheeling diodes.

**Table 1: Device summary**

Symbol	Value
I <sub>F(AV)</sub>	up to 2 x 120 A
V <sub>RRM</sub>	600 V
T <sub>j</sub> (max.)	150 °C
V <sub>F</sub> (typ.)	0.95 V
t <sub>rr</sub> (max.)	80 ns



TM: ISOTOP is a trademark of  
STMicroelectronics

# 1 Characteristics

Table 2: Absolute ratings (limiting values, per diode)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	600	V
$I_{F(RMS)}$	Forward rms current	180	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_c = 65 \text{ }^\circ\text{C}$ , per diode	100
		$T_c = 35 \text{ }^\circ\text{C}$ , per diode	120
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal}$	800
$T_{stg}$	Storage temperature range	-55 to +150	${}^\circ\text{C}$
$T_j$	Maximum operating junction temperature	150	${}^\circ\text{C}$

Table 3: Thermal parameters

Symbol	Parameter	Maximum values	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.60
		Total	0.35
$R_{th(c)}$	Coupling	0.1	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode1}) = P_{(\text{diode1})} \times R_{th(j-c)} \text{ (per diode)} + P_{(\text{diode2})} \times R_{th(c)}$$

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_{R(1)}$	Reverse leakage current	$T_j = 25 \text{ }^\circ\text{C}$	$V_R = V_{RRM}$	-		100	$\mu\text{A}$
		$T_j = 125 \text{ }^\circ\text{C}$		-	100	1000	
$V_F(2)$	Forward voltage drop	$T_j = 25 \text{ }^\circ\text{C}$	$I_F = 100 \text{ A}$	-		1.55	V
		$T_j = 150 \text{ }^\circ\text{C}$		-	0.95	1.20	

## Notes:

(1)Pulse test:  $t_p = 5 \text{ ms}$ ,  $\delta < 2\%$

(2)Pulse test:  $t_p = 380 \text{ } \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the maximum conduction losses, use the following equation:

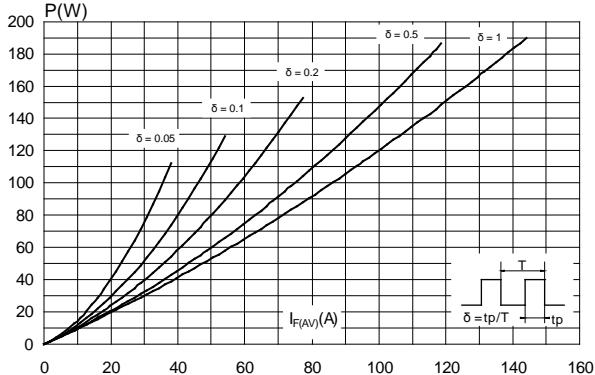
$$P = 0.93 \times I_{F(AV)} + 0.0027 \times I_{F(RMS)}^2$$

Table 5: Dynamic characteristics (per diode)

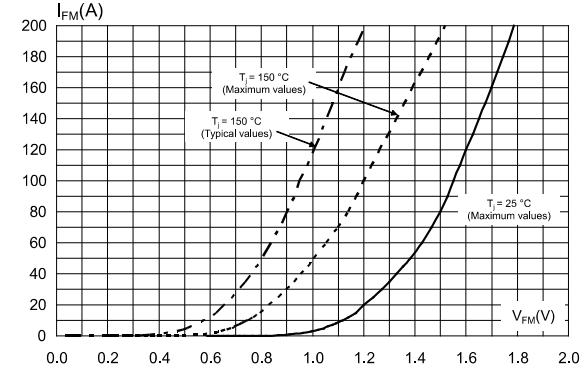
Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$T_j = 25 \text{ }^\circ\text{C}$	$I_F = 0.5 \text{ A},$ $I_{rr} = 0.25 \text{ A},$ $I_R = 1 \text{ A}$	-		80	ns
			$I_F = 1 \text{ A},$ $dI_F/dt = 50 \text{ A}/\mu\text{s},$ $V_R = 30 \text{ V}$	-	85	120	
$I_{RM}$	Reverse recovery current	$T_j = 125 \text{ }^\circ\text{C}$	$I_F = 100 \text{ A},$ $dI_F/dt = 400 \text{ A}/\mu\text{s},$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	15	20	A
$t_{fr}$	Forward recovery time	$T_j = 25 \text{ }^\circ\text{C}$	$I_F = 100 \text{ A},$ $dI_F/dt = 200 \text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$	-		700	ns
$V_{FP}$	Forward recovery voltage	$T_j = 25 \text{ }^\circ\text{C}$	$I_F = 100 \text{ A},$ $dI_F/dt = 200 \text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$	-	3.4		V

## 1.1 Characteristics (curves)

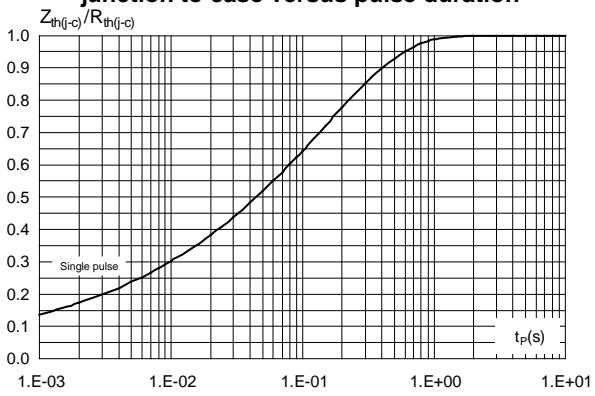
**Figure 1: Conduction losses versus average forward current (per diode)**



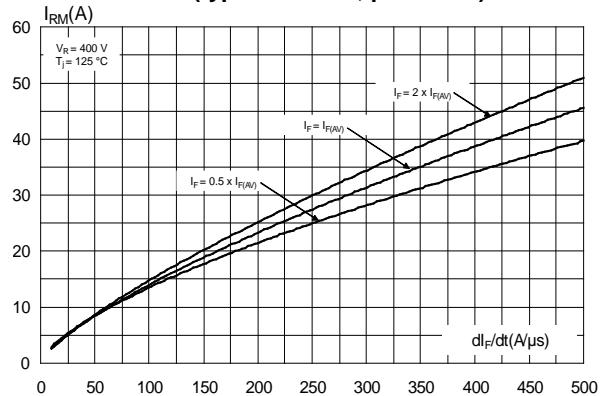
**Figure 2: Forward voltage drop versus forward current (per diode)**



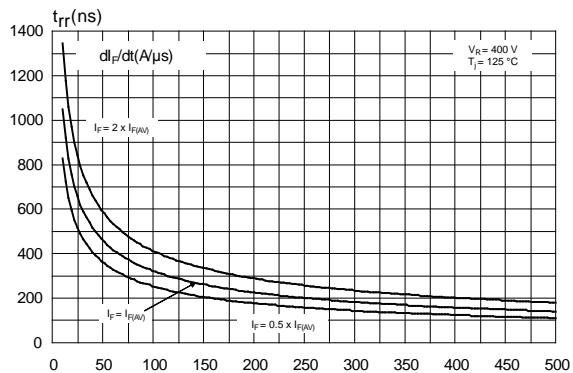
**Figure 3: Relative variation of thermal impedance junction to case versus pulse duration**



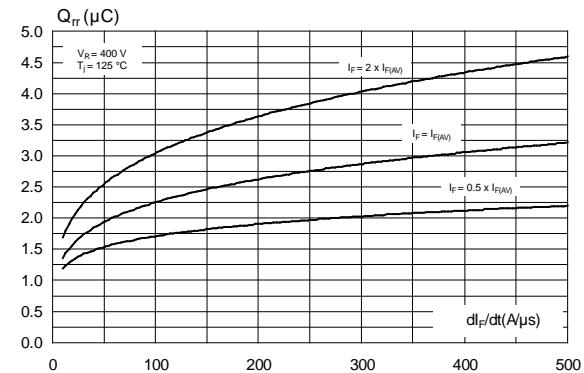
**Figure 4: Peak reverse recovery current versus  $dI/dt$  (typical values, per diode)**



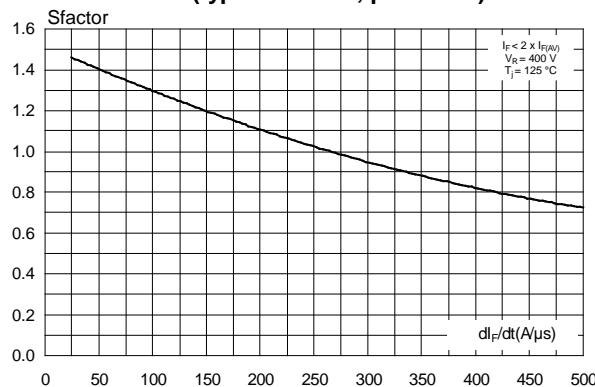
**Figure 5: Reverse recovery time versus  $dI/dt$  (typical values, per diode)**



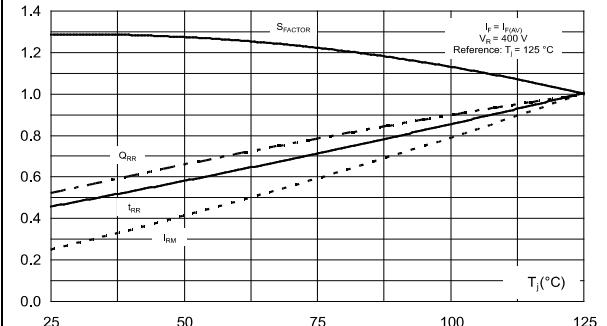
**Figure 6: Reverse recovery charges versus  $dI/dt$  (typical values, per diode)**



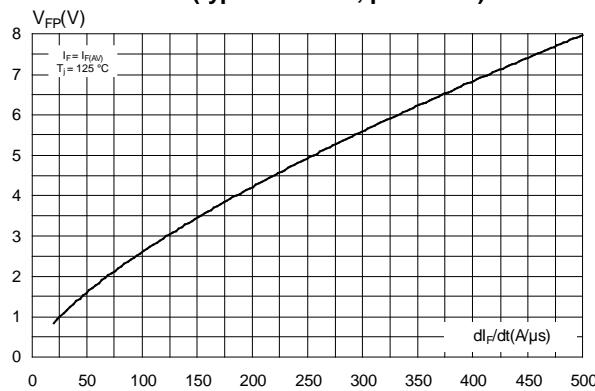
**Figure 7: Reverse recovery softness factor versus  $dl_f/dt$  (typical values, per diode)**



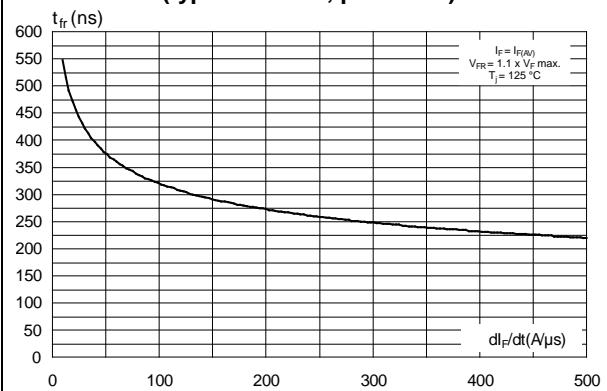
**Figure 8: Relative variations of dynamic parameters versus junction temperature**



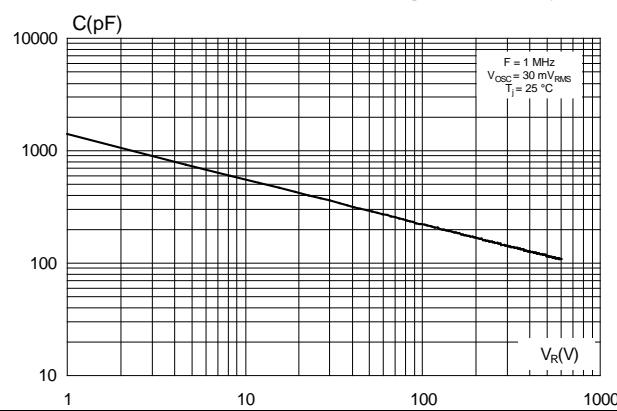
**Figure 9: Transient peak forward voltage versus  $dl_f/dt$  (typical values, per diode)**



**Figure 10: Forward recovery time versus  $dl_f/dt$  (typical values, per diode)**



**Figure 11: Junction capacitance versus reverse voltage applied (typical values, per diode)**



## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com).  
ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 1.3 N·m
- Maximum torque value: 1.5 N·m

STMicroelectronics strongly recommends the use of the screws delivered with this product.

The use of any other screws is entirely at the user's own risk and will invalidate the warranty.

## 2.1 ISOTOP package information

Figure 12: ISOTOP package outline

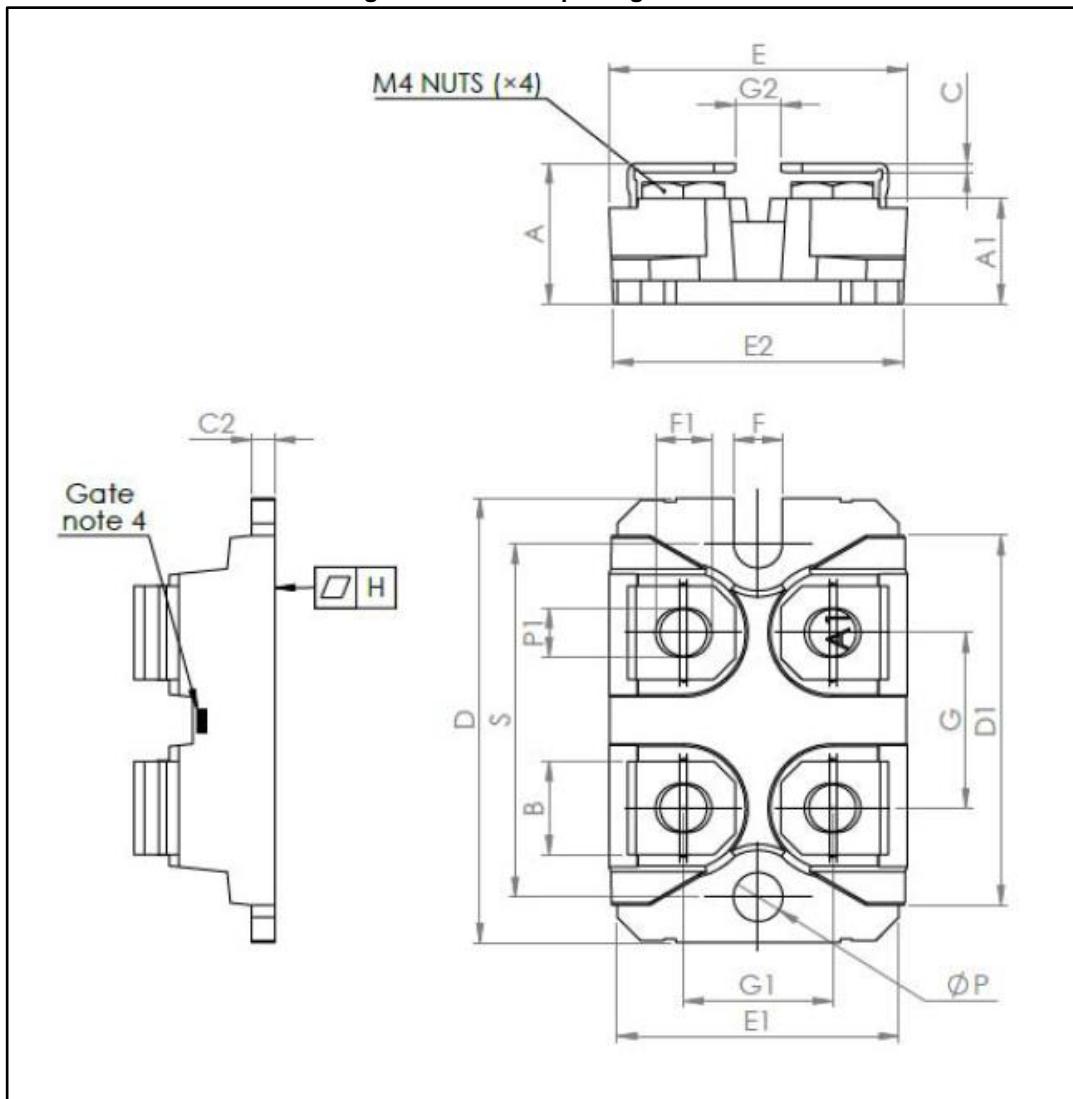


Table 6: ISOTOP package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.460	0.480
A1	8.90	9.10	0.350	0.358
B	7.80	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80		0.976	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5	0.181	0.197
H	-0.05	0.1	-0.002	0.004
Diam P	4	4.30	0.157	0.69
P1	4	4.30	0.157	0.69
S	30.10	30.30	1.185	1.193

### 3 Ordering information

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STTH200L06TV1	STTH200L06TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

### 4 Revision history

Table 8: Document revision history

Date	Revision	Changes
07-Sep-2004	1	First issue.
05-Sep-2011	2	Updated <i>Figure 6</i> .
06-Nov-2017	3	Updated <a href="#">Section "Features"</a> and <a href="#">Section 2.1: "ISOTOP package information"</a> .

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